

Switch-mode Power Rectifiers

MBR1080G, MBR1090G, MBR10100G, NRVB10100G

Features

- Guard-Ring for Stress Protection
- Low Forward Voltage
- 175°C Operating Junction Temperature
- Epoxy Meets UL 94 V-0 @ 0.125 in
- Low Power Loss/High Efficiency
- High Surge Capacity
- Low Stored Charge Majority Carrier Conduction
- AEC-Q101 Qualified and PPAP Capable
- NRVB Prefix for Automotive and Other Applications Requiring Unique Site and Control Change Requirements
- All Packages are Pb–Free*

Mechanical Characteristics

- Case: Epoxy, Molded
- Weight: 1.9 Grams (Approximately)
- Finish: All External Surfaces Corrosion Resistant and Terminal Leads are Readily Solderable
- Lead Temperature for Soldering Purposes: 260°C Max. for 10 Seconds
- ESD Rating:
 - ♦ Human Body Model = 3B
 - ♦ Machine Model = C

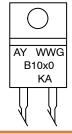
SCHOTTKY BARRIER RECTIFIERS 10 AMPERES, 80 to 100 VOLTS



TO-220AC CASE 221B



MARKING DIAGRAM



A = Assembly Location
Y = Year
WW = Work Week
G = Pb-Free Package
B10x0 = Device Code
x = 8, 9 or 10
KA = Diode Polarity

ORDERING INFORMATION

| Device | Package | Shipping |
|-----------|---------------------|---------------|
| MBR10100G | TO-220 (Pb-Free) | 50 Units/Rail |

DISCONTINUED (Note 1)

1

| MBR1080G | TO-220 (Pb-Free) | 50 Units/Rail |
|------------|---------------------|---------------|
| MBR1090G | TO-220 (Pb-Free) | 50 Units/Rail |
| NRVB10100G | TO-220 (Pb-Free) | 50 Units/Rail |

- †For information on tape and reel specifications, including part orientation and tape sizes, please refer to our Tape and Reel Packaging Specifications Brochure, BRD8011/D.
- DISCONTINUED: This device is not recommended for new design. Please contact your onsemi representative for information. The most current information on this device may be available on www.onsemi.com.

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MAXIMUM RATINGS

| Rating | | MBR/NRVB | | | |
|--|--|--------------|------|-------|------|
| | | 1080 | 1090 | 10100 | Unit |
| Peak Repetitive Reverse Voltage Working Peak Reverse Voltage DC Blocking Voltage | V _{RRM} V _{RWM} V _R | 80 | 90 | 100 | V |
| Average Rectified Forward Current (Rated V _R) T _C = 133°C | I _{F(AV)} | 10 | | Α | |
| Peak Repetitive Forward Current (Rated V _R , Square Wave, 20 kHz) T _C = 133°C | I _{FRM} | 20 | | Α | |
| Nonrepetitive Peak Surge Current (Surge applied at rated load conditions halfwave, single phase, 60 Hz) | I _{FSM} | 150 | | Α | |
| Peak Repetitive Reverse Surge Current (2.0 μs, 1.0 kHz) | I _{RRM} | 0.5 | | Α | |
| Operating Junction Temperature (Note 1) | T _J | - 65 to +175 | | °C | |
| Storage Temperature | T _{stg} | - 65 to +175 | | °C | |
| Voltage Rate of Change (Rated V _R) dv/dt 10,000 | | | V/μs | | |

Stresses exceeding Maximum Ratings may damage the device. Maximum Ratings are stress ratings only. Functional operation above the Recommended Operating Conditions is not implied. Extended exposure to stresses above the Recommended Operating Conditions may affect device reliability.

THERMAL CHARACTERISTICS

| Characteristic | Symbol | Value | Unit |
|---|----------------|-------|------|
| Maximum Thermal Resistance, Junction-to-Case | $R_{	heta JC}$ | 2.0 | °C/W |
| Maximum Thermal Resistance, Junction-to-Ambient | $R_{	heta JA}$ | 60 | °C/W |

ELECTRICAL CHARACTERISTICS

| Characteristic | Symbol | Value | Unit |
|--|----------------|----------------------------|------|
| Maximum Instantaneous Forward Voltage (Note 2) ($i_F = 10$ Amps, $T_C = 125$ °C) ($i_F = 10$ Amps, $T_C = 25$ °C) ($i_F = 20$ Amps, $T_C = 125$ °C) ($i_F = 20$ Amps, $T_C = 25$ °C) | VF | 0.7 0.8 0.85 0.95 | V |
| Maximum Instantaneous Reverse Current (Note 2) (Rated dc Voltage, $T_C = 125^{\circ}C$) (Rated dc Voltage, $T_C = 25^{\circ}C$) | i _R | 6.0 0.10 | mA |

^{2.} Pulse Test: Pulse Width = 300 μ s, Duty Cycle \leq 2.0%.

^{1.} The heat generated must be less than the thermal conductivity from Junction–to–Ambient: $dP_D/dT_J < 1/R_{\theta JA}$.

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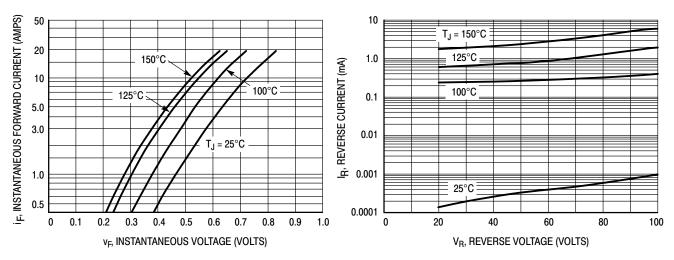


Figure 1. Typical Forward Voltage

Figure 2. Typical Reverse Current

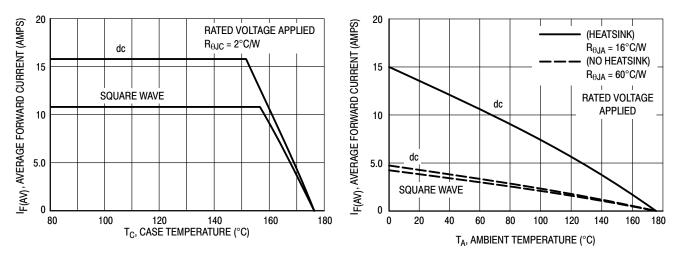


Figure 3. Typical Current Derating, Case

Figure 4. Typical Current Derating, Ambient

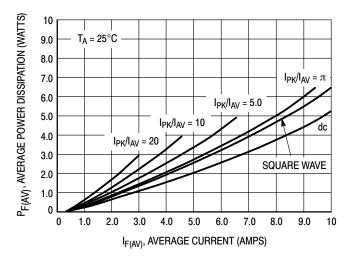


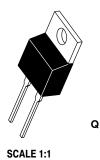
Figure 5. Forward Power Dissipation

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REVISION HISTORY

| Revision | Description of Changes | Date |
|----------|---|-----------|
| 2 | MBR1080G, MBR1090G, NRVB10100G OPN Marked as Discontinued + Rebranded the Data Sheet to onsemi format | 6/23/2025 |





TO-220, 2-LEAD CASE 221B-04 ISSUE F

DATE 12 APR 2013

- 1. DIMENSIONING AND TOLERANCING PER ANSI Y14.5M, 1982. 2. CONTROLLING DIMENSION: INCH.

| | INCHES | | MILLIN | IETERS |
|-----|--------|-------|--------|--------|
| DIM | MIN | MAX | MIN | MAX |
| Α | 0.595 | 0.620 | 15.11 | 15.75 |
| В | 0.380 | 0.405 | 9.65 | 10.29 |
| С | 0.160 | 0.190 | 4.06 | 4.82 |
| D | 0.025 | 0.039 | 0.64 | 1.00 |
| F | 0.142 | 0.161 | 3.61 | 4.09 |
| G | 0.190 | 0.210 | 4.83 | 5.33 |
| Н | 0.110 | 0.130 | 2.79 | 3.30 |
| J | 0.014 | 0.025 | 0.36 | 0.64 |
| K | 0.500 | 0.562 | 12.70 | 14.27 |
| L | 0.045 | 0.060 | 1.14 | 1.52 |
| Q | 0.100 | 0.120 | 2.54 | 3.04 |
| R | 0.080 | 0.110 | 2.04 | 2.79 |
| S | 0.045 | 0.055 | 1.14 | 1.39 |
| T | 0.235 | 0.255 | 5.97 | 6.48 |
| U | 0.000 | 0.050 | 0.000 | 1.27 |

STYLE 1: PIN 1. CATHODE 2. N/A 3. ANODE

STYLE 2: PIN 1. ANODE 2. N/A 3. CATHODE 4. ANODE

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